

P-channel -30 V, 11 mΩ typ., -45 A STripFET™ H6 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

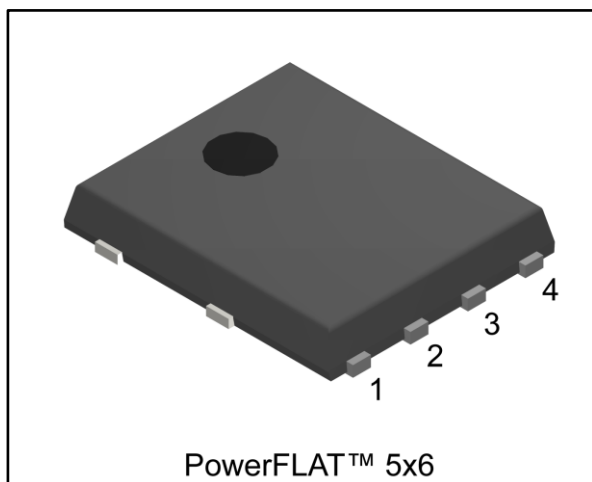
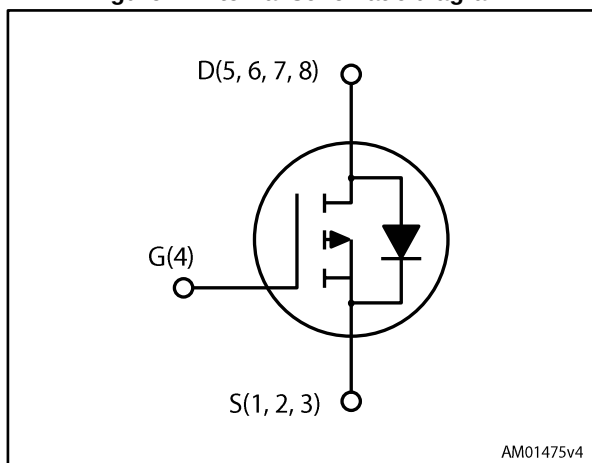


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max	I _D
STL45P3LLH6	-30 V	13 mΩ	-45 A

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is a P-channel Power MOSFET developed using the STripFET™ H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packing
STL45P3LLH6	45P3LLH6	PowerFLAT™ 5x6	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	-30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	-45	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	-34	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	-12	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^{\circ}\text{C}$	-8.7	A
$I_{DM}^{(1)(3)}$	Drain current (pulsed)	-180	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	-48	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	75	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	4.8	W
T_{stg}	Storage temperature range	- 55 to 175	$^{\circ}\text{C}$
T_j	Operating junction temperature range		

Notes:⁽¹⁾The value is rated according to R_{thj-c} .⁽²⁾This value is rated according to $R_{thj-pcb}$ ⁽³⁾Pulse width is limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.00	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^{\circ}\text{C/W}$

Notes:⁽¹⁾When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10\text{ sec}$

2 Electrical characteristics

($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = -1\text{ mA}$	-30			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = -30\text{ V}$			-1	μA
		$V_{GS} = 0, V_{DS} = -30\text{ V}, T_C = 125\text{ }^{\circ}\text{C}$ ⁽¹⁾			-10	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1			V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = -10\text{ V}, I_D = -6\text{ A}$		11	13	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -6\text{ A}$		16	19.5	$\text{m}\Omega$

Notes:

⁽¹⁾ Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	2615	-	pF
C_{oss}	Output capacitance		-	340	-	pF
C_{rss}	Reverse transfer capacitance		-	235	-	pF
Q_g	Total gate charge	$V_{DD} = -15\text{ V}, I_D = -12\text{ A}, V_{GS} = -4.5\text{ V}$	-	24	-	nC
Q_{gs}	Gate-source charge		-	9	-	nC
Q_{gd}	Gate-drain charge		-	8	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = -15\text{ V}, I_D = -6\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = -10\text{ V}$	-	13.2	-	ns
t_r	Rise time		-	93	-	ns
$t_{d(off)}$	Turn-off delay time		-	50	-	ns
t_f	Fall time		-	18	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = -6\text{ A}$, $V_{GS} = 0$	-		-1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = -6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = -16\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	20		ns
Q_{rr}	Reverse recovery charge		-	16		nC
I_{RRM}	Reverse recovery current		-	-1.6		A

Notes:

⁽¹⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.2 Electrical characteristics (curves)



Note: For the P-channel Power MOSFET, current and voltage polarities are reversed.

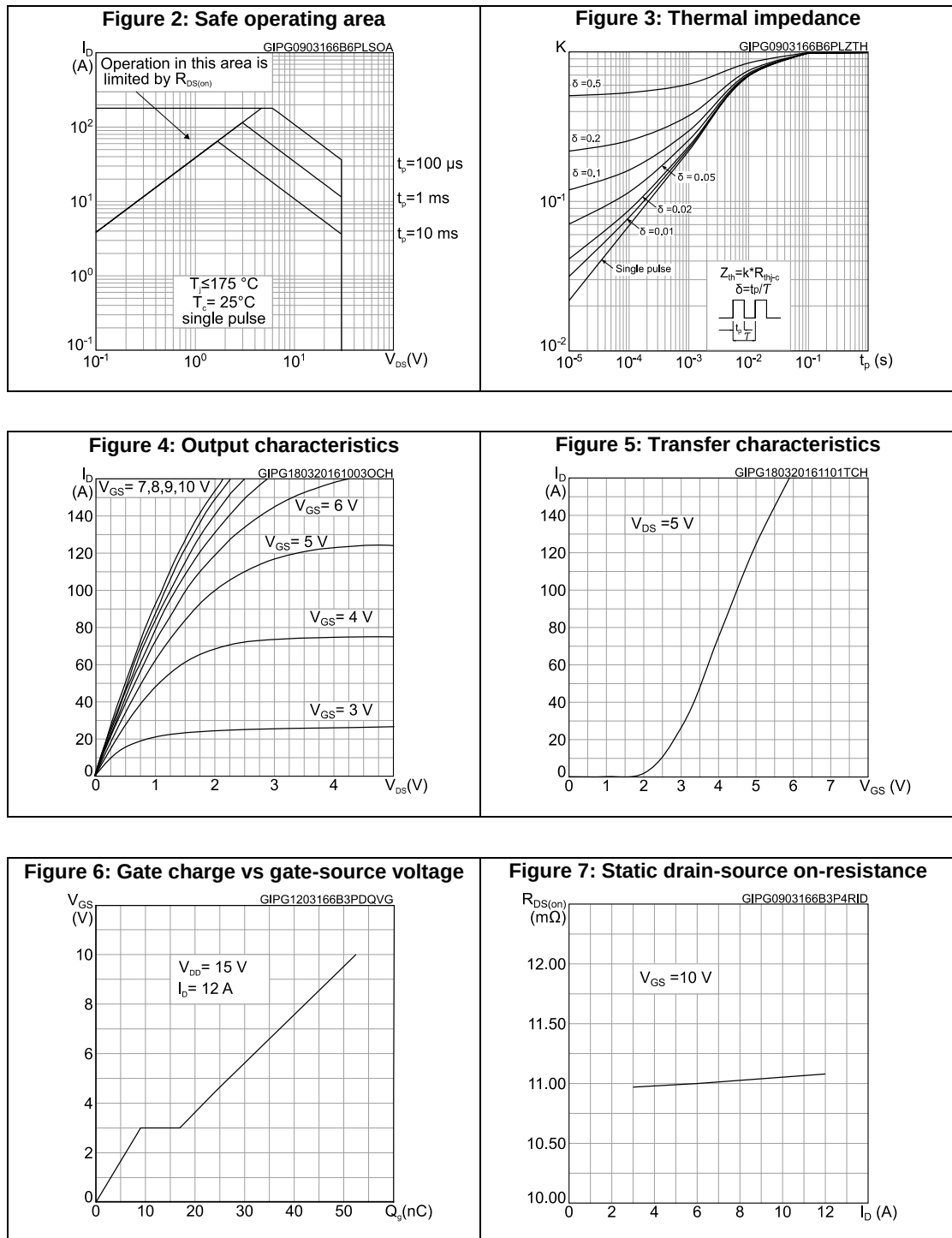


Figure 8: Capacitance variations

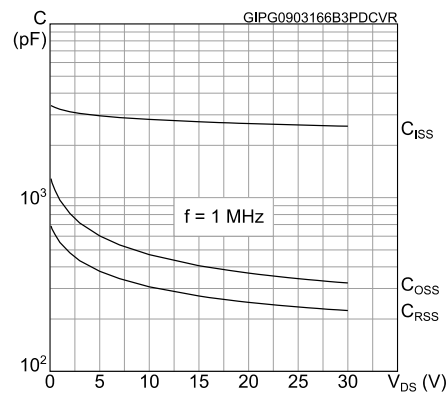


Figure 9: Normalized gate threshold voltage vs temperature

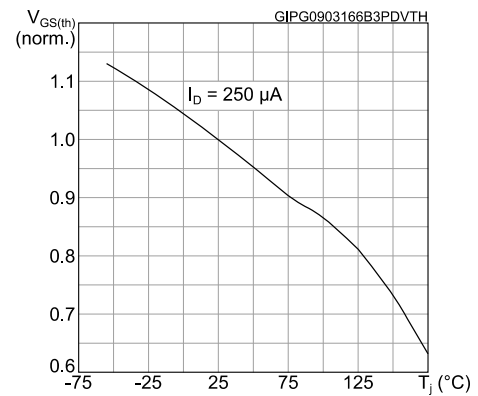


Figure 10: Normalized on-resistance vs temperature

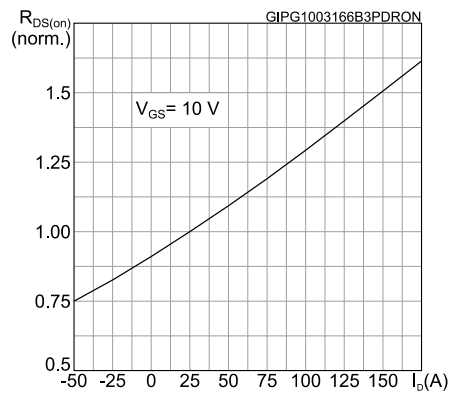
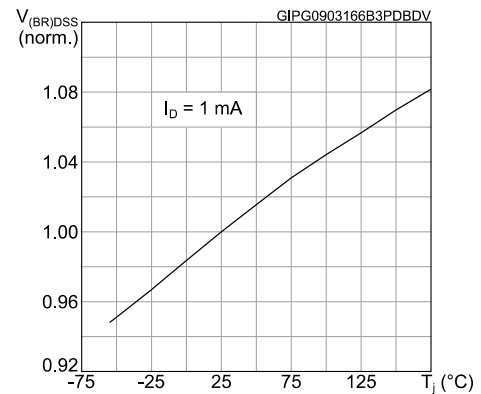
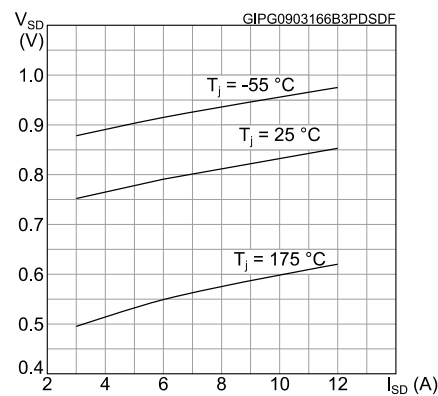
Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Switching times test circuit for resistive load

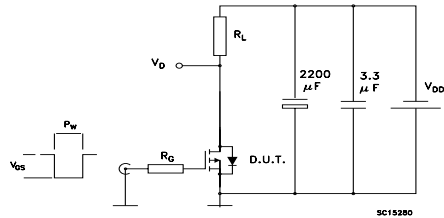


Figure 14: Gate charge test circuit

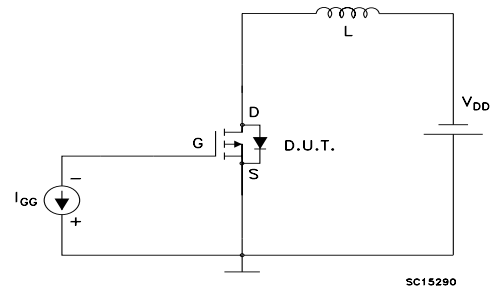
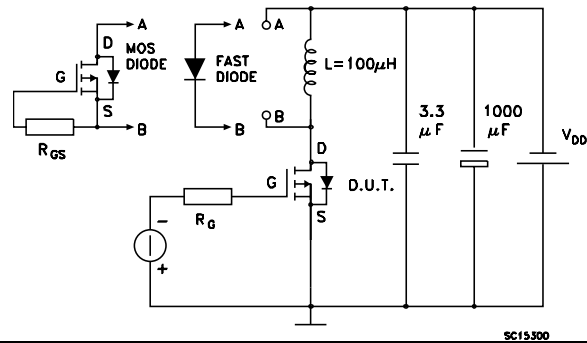


Figure 15: Test circuit for inductive load switching and diode recovery times



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK[®] is an ST trademark.

4.1 PowerFLAT™ 5x6 package information

Figure 16: PowerFLAT™ 5x6 type R package outline

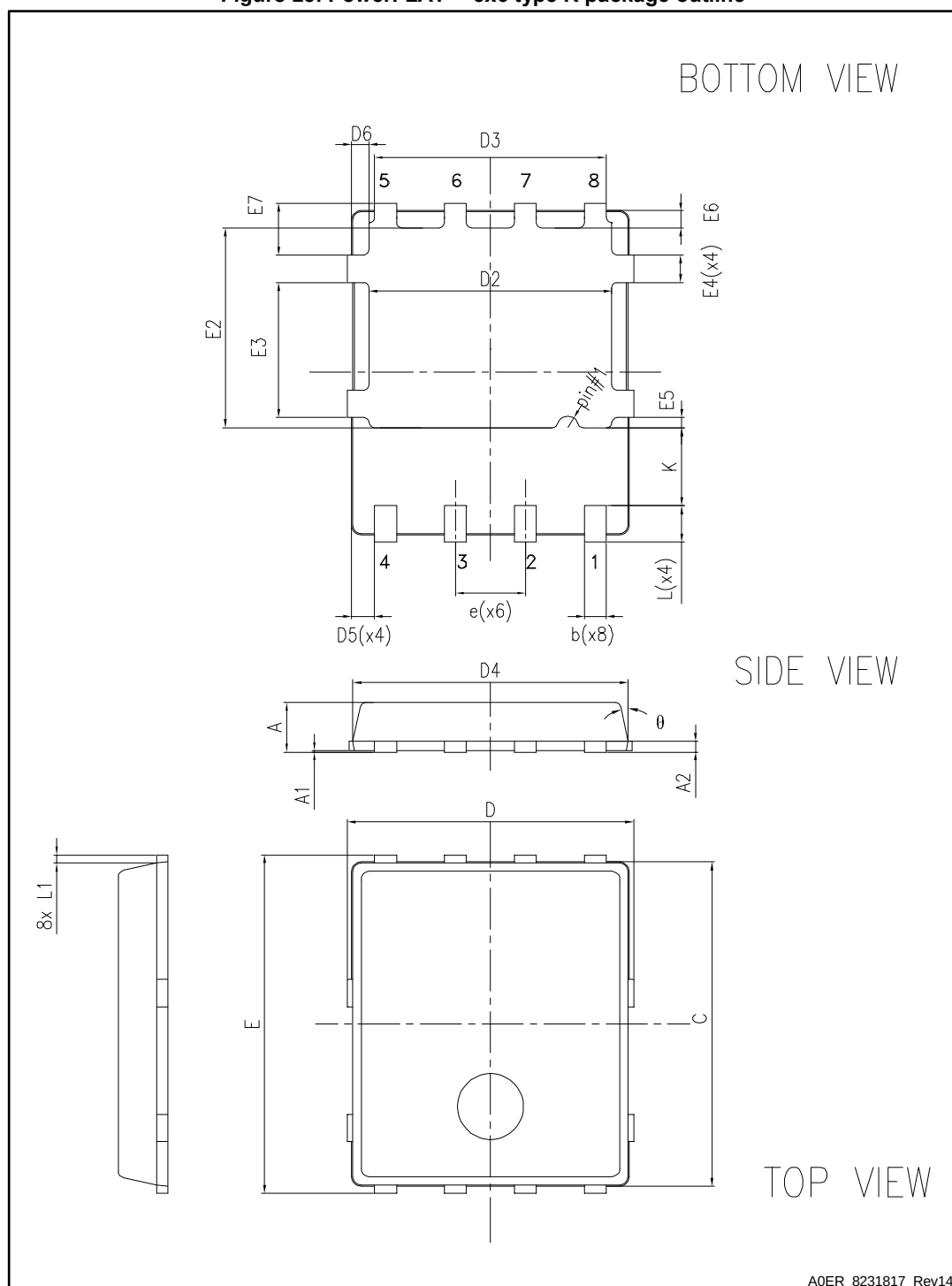
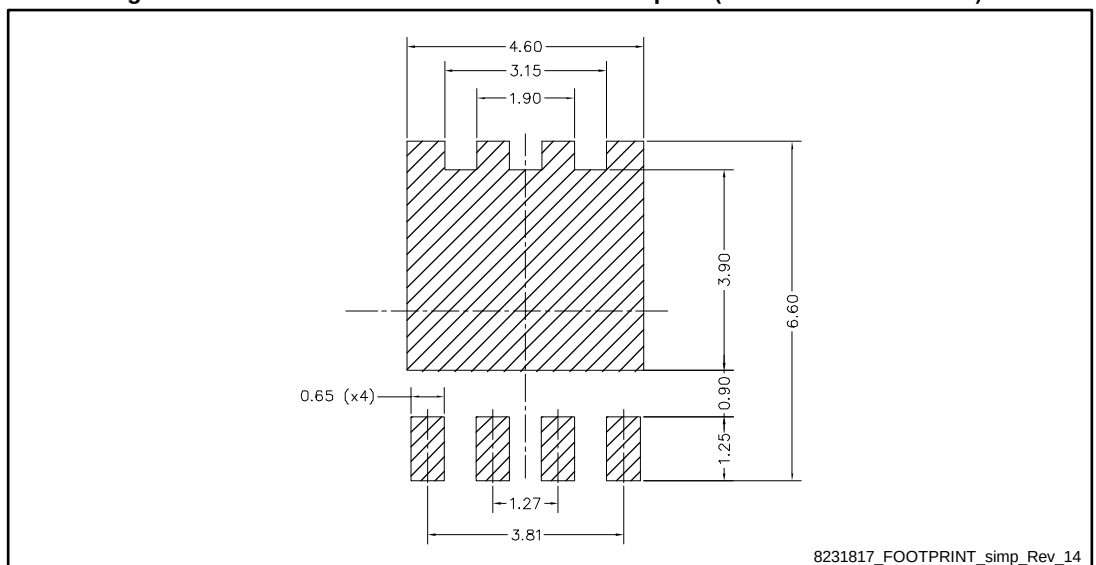


Table 8: PowerFLAT™ 5x6 type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
K	1.275		1.575
L	0.60		0.80
L1	0.05	0.15	0.25
θ		0°	12°

Figure 17: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 packaging information

Figure 18: PowerFLAT™ 5x6 tape (dimensions are in mm)

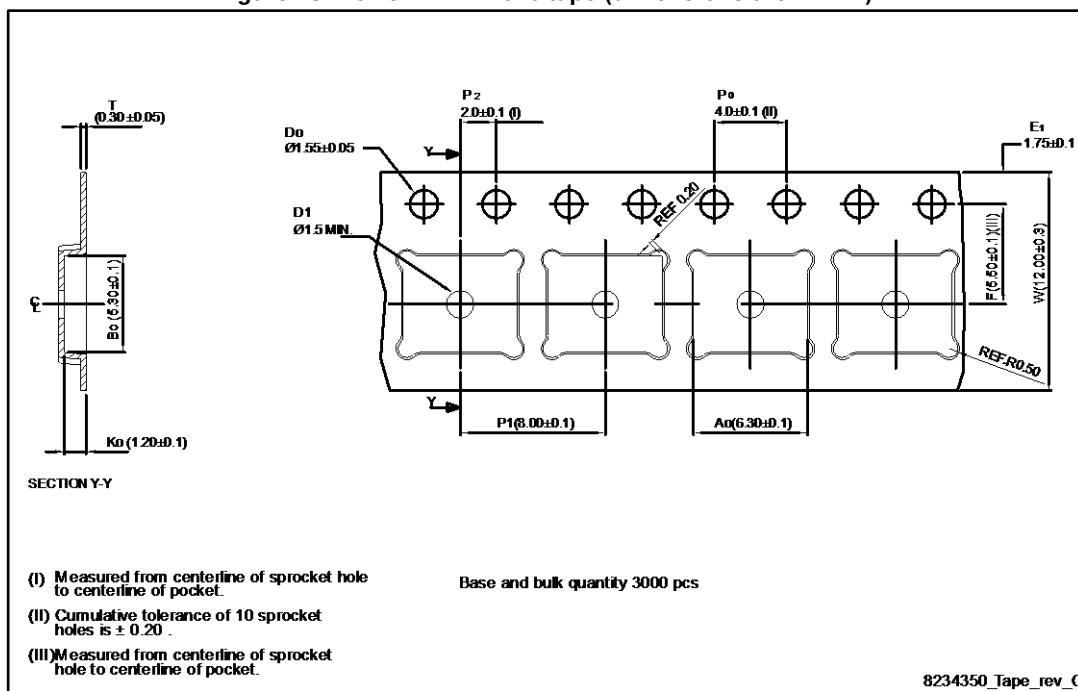


Figure 19: PowerFLAT™ 5x6 package orientation in carrier tape

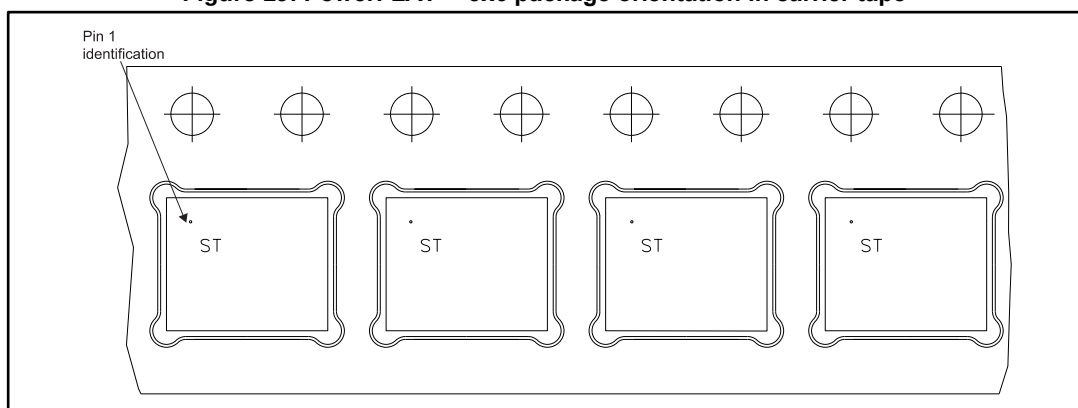
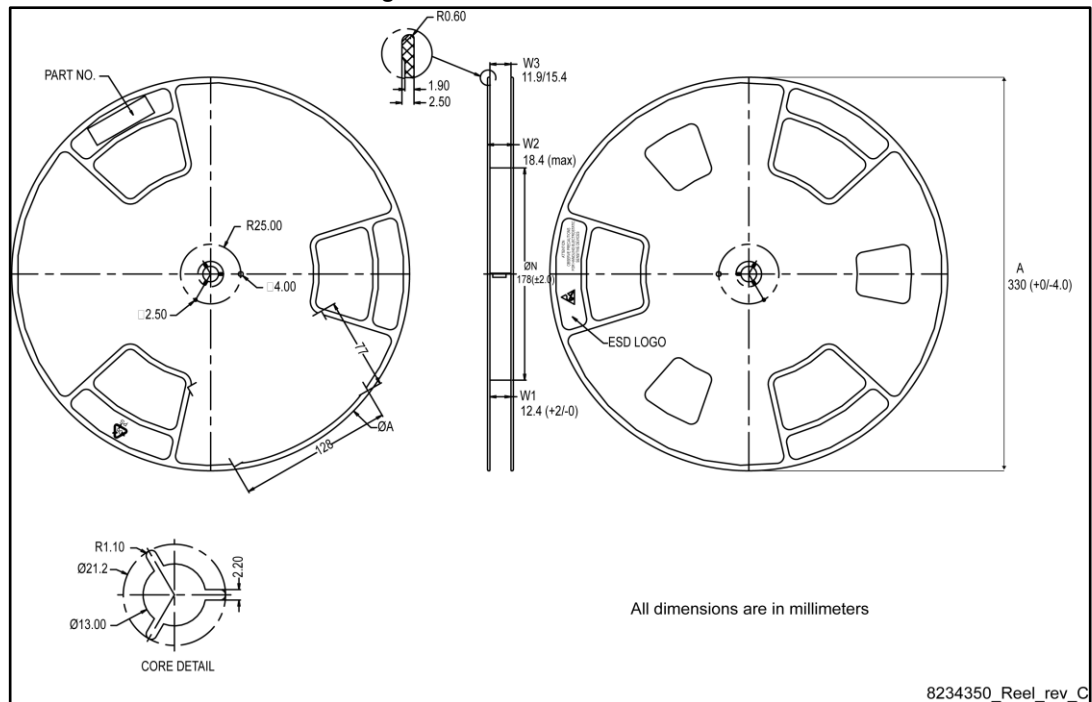


Figure 20: PowerFLAT™ 5x6 reel



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
01-Apr-2016	1	First release.

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